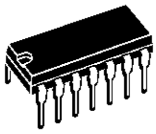
QUAD EXCLUSIVE OR GATE

- MEDIUM-SPEED OPERATION : t_{PD} = 65ns (Typ.) at V_{DD} = 10V
- LOW OUTPUT IMPEDANCE : 500Ω (Typ.) AT V_{DD} - V_{SS} = 10V
- QUIESCENT CURRENT SPECIFIED UP TO 20V
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT I_I = 100nA (MAX) AT V_{DD} = 18V T_A = 25°C
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B " STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"



DIP

ORDER CODES

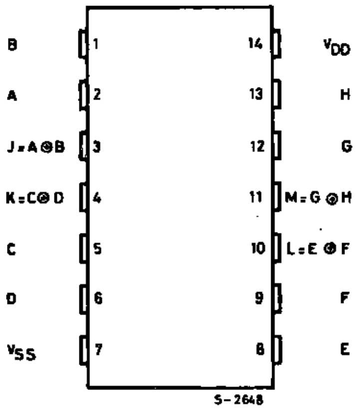
PACKAGE	TUBE	T & R
DIP	CC4030	

DESCRIPTION

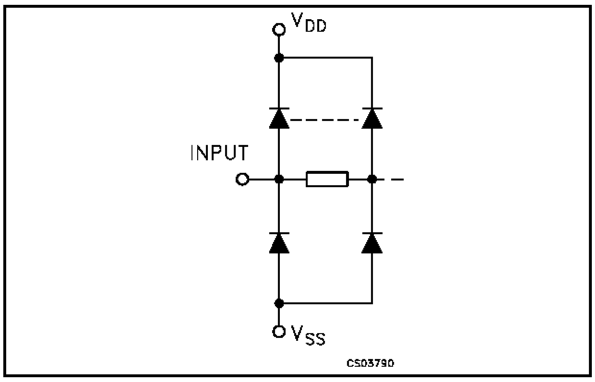
The CC4030 is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages.

The CC4030 type consists of four independent exclusive OR gates integrated on a single monolithic silicon chip. Each exclusive-OR gate consists of four n-channel and four p-channel enhancement type transistors. All inputs and outputs are protected against electrostatics effects.

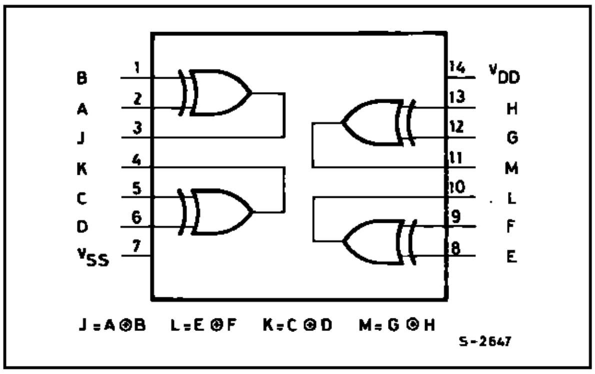
PIN CONNECTION



INPUT EQUIVALENT CIRCUIT



LOGIC DIAGRAM



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 2, 5, 6, 8, 9, 12, 13	B, A, C, D, E, F, G, H	Data Inputs
3, 4, 10, 11	J, K, L, M	Data Outputs
7	V_{SS}	Negative Supply Voltage
14	V_{DD}	Positive Supply Voltage

TRUTH TABLE

INPUTS		OUTPUT
B, C, E, G	**A, D, F, H**	**J, K, L, M**
L	L	L
L	H	H
H	L	H
H	H	L

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	-0.5 to +20	V
V_I	DC Input Voltage	-0.5 to V_{DD} + 0.5	V
I_I	DC Input Current	± 10	mA
P_D	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T_{op}	Operating Temperature	-55 to +125	°C
T_{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.
All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	3 to 1 8	V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature	-55 to 125	°C

DC SPECIFICATIONS

Symbol	Parameter	Test Condition				Value							Unit
		V_I (V)	V_O (V)	$\|I_O\|$ (µA)	V_{DD} (V)	T_A = 25°C			-40 to 85°C		-55 to 125°C		
						Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
I_L	Quiescent Current	0/5			5		0.02	1		30		30	µA
		0/10			10		0.02	2		60		60	
		0/15			15		0.02	4		120		120	
		0/18			18		0.04	20		600		600	
V_{OH}	High Level Output Voltage	0/5		<1	5	4.95			4.95		4.95		V
		0/10		<1	10	9.95			9.95		9.95		
		0/15		<1	15	14.95			14.95		14.95		
V_{OL}	Low Level Output Voltage	5/0		<1	5		0.05			0.05		0.05	V
		10/0		<1	10		0.05			0.05		0.05	
		15/0		<1	15		0.05			0.05		0.05	
V_{IH}	High Level Input Voltage		0.5/4.5	<1	5	3.5			3.5		3.5		V
			1/9	<1	10	7			7		7		
			1.5/13.5	<1	15	11			11		11		
V_{IL}	Low Level Input Voltage		4.5/0.5	<1	5			1.5		1.5		1.5	V
			9/1	<1	10			3		3		3	
			13.5/1.5	<1	15			4		4		4	
I_{OH}	Output Drive Current	0/5	2.5	<1	5	-1.36	-3.2		-1.15		-1.1		mA
		0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		
		0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
I_{OL}	Output Sink Current	0/5	0.4	<1	5	0.44	1		0.36		0.36		mA
		0/10	0.5	<1	10	1.1	2.6		0.9		0.9		
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		
I_I	Input Leakage Current	0/18	Any Input		18		$\pm 10^{-5}$	±0.1		±1		±1	µA
C_I	Input Capacitance		Any Input				5	7.5					pF

The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD}=5V, 2V min. with V_{DD}=10V, 2.5V min. with V_{DD}=15V

DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200KΩ, $t_r = t_f$ = 20 ns)

Symbol	Parameter	Test Condition		Value (*)			Unit
		V_{DD} (V)		Min.	Typ.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time	5			140	280	ns
		10			65	130	
		15			50	100	
t_{TLH} t_{THL}	Output Transition Time	5			100	200	ns
		10			50	100	
		15			40	80	

(*) Typical temperature coefficient for all V_{DD} value is 0.3 %/°C.